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DESCRIPTION:

The DP5Z2MX16PAn3 SLCC devices are a revolutionary new memory subsystem using Dense-Pac Microsystems ceramic Stackable Leadless Chip Carriers (SLCC). Available unleaded, straight leaded, J leaded, gullwing leaded packages, or mounted on a 50-pin PGA co-fired ceramic substrate. The Device packs 32-Megabits of FLASH EEPROM in an area as small as 0.463 in² while maintaining a total height as low as 0.171 inches.

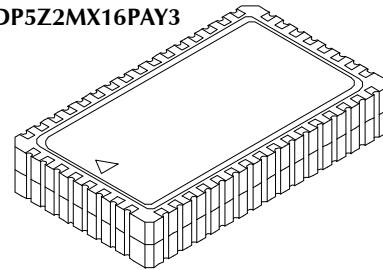
The DP5Z2MX16PAn3 is a 2 Meg x 8 FLASH EEPROM based memory module. Each SLCC is hermetically sealed making the module suitable for commercial, industrial and military applications.

By using SLCCs, the Stack family of modules offer a higher board density of memory than available with conventional through-hole, surface mount or hybrid techniques.

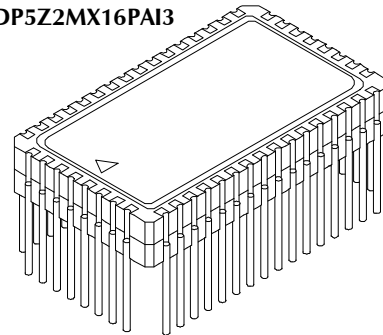
FEATURES:

- Organization: 2 Meg x 16
- Fast Access Times: 70*, 90, 120, 150ns (max.)
* V_{DD} = 5.0V ± 5%
- Single 5.0 Volt Power Supply
- High-Density Symmetrically Blocked Architecture
 - 32 Uniform Sectors of 64 Kbytes Each
- Extended Cycling Capability
 - 100,000 Write/Erase Cycles per Sector
- Automated Erase and Program Cycles
 - Command User Interface
 - Status Register
- SRAM-Compatible Write Interface
- Hardware Data Protection Feature
 - Erase / Write Lockout during Power Transitions
- Packages Available:
 - DP5Z2MX16PAY3 48 - Pin SLCC
 - DP5Z2MX16PAI3 48 - Pin Straight Leaded SLCC
 - DP5Z2MX16PAH3 48 - Pin Gullwing Leaded SLCC
 - DP5Z2MX16PAJ3 48 - Pin J Leaded SLCC
 - DP5Z2MX16PAA3 50 - Pin PGA Dense-SLCC

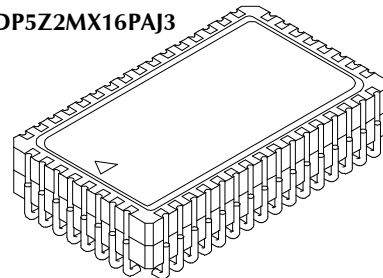
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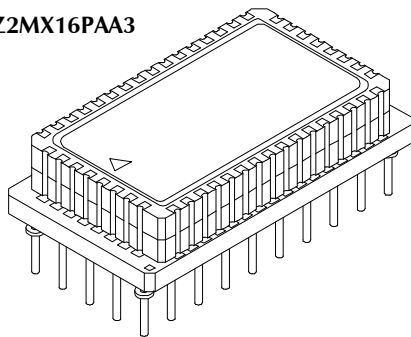
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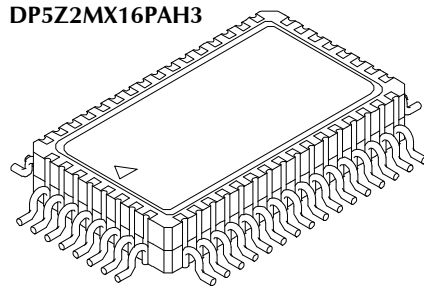
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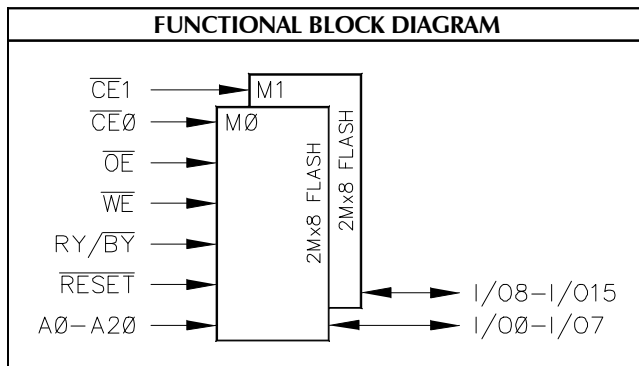
DP5Z2MX16PAA3



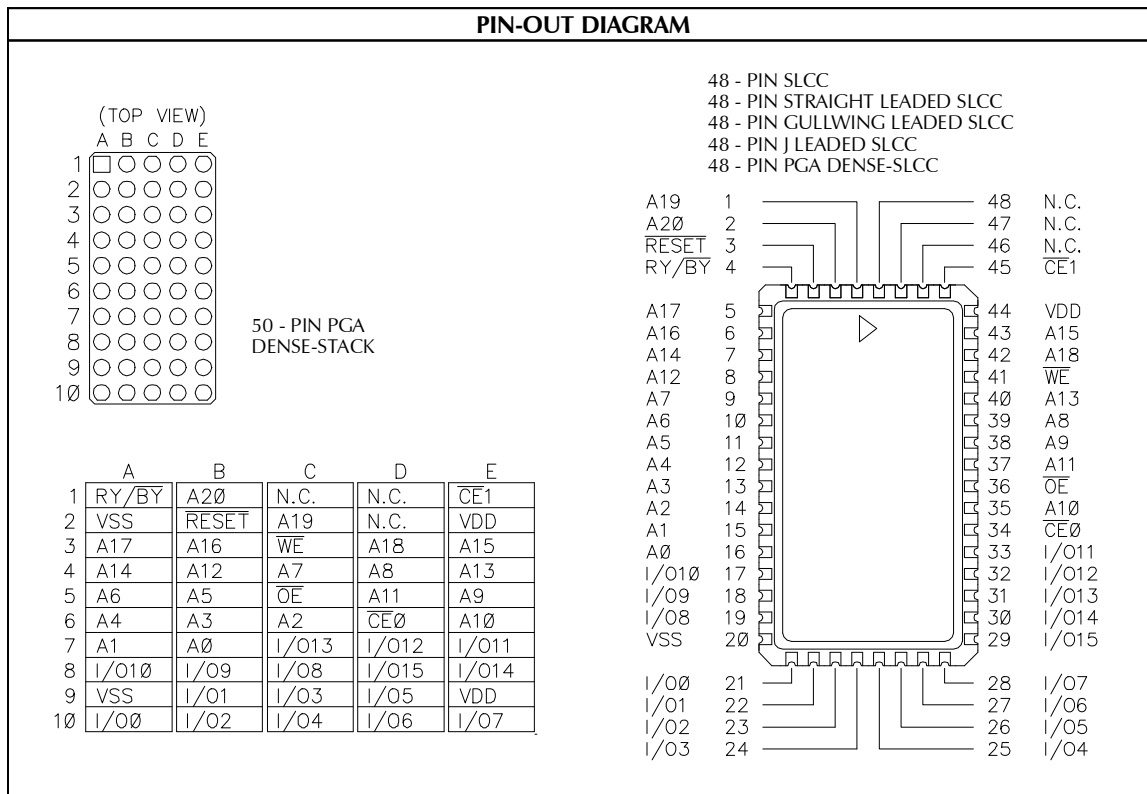
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PIN NAMES	
A0 - A20	Address
I/O0 - I/O15	Data Inputs/Outputs
CE0, CE1	Chip Enables
WE	Write Enable
OE	Output Enable
RESET	Hardware reset Pin, Active Low
RY/BY	Ready/Busy Output
VDD	Single Power (+5.0V)
VSS	Ground
N.C.	No Connect



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BUS OPERATION

This section describes the requirements and use of the device bus operations, which are initiated through the internal command register. The command register itself does not occupy any addressable memory locations. The register is composed of latches that store the commands, along with the address and data information needed to execute the command. The contents of

the register serve as inputs to the internal state machine. The state machine outputs dictate the function of the device. The appropriate device bus operations table lists the inputs and control levels required, and the resulting output. The following subsections describe each of these operations in further detail.

Table 1. Device Bus Operation

Operation	\overline{CE}	\overline{OE}	\overline{WE}	\overline{RESET}	A0 - A20	I/O0 - I/O7 ⁹
Read	L	L	H	H	A _{IN}	D _{OUT}
Write	L	H	L	H	A _{IN}	D _{IN}
CMOS Standby	V _{DD} ± 0.5V	X	X	V _{DD} ± 0.5V	X	HIGH-Z
TTL Standby	H	X	X	H	X	HIGH-Z
Output Disable	L	H	H	H	X	HIGH-Z
Hardware Reset	X	X	X	L	X	HIGH-Z
Temporary Sector Unprotect (See Note)	X	X	X	V _{ID}	A _{IN}	D _{IN}

Legend: L = Logic LOW = V_{IL}, H = Logic HIGH = V_{IH}, V_{ID} = 12.0±0.5V, X = Don't Care, D_{IN} = Data In, D_{OUT} = Data Out, A_{IN} = Address In

Requirements for Reading Array Data

To read array data from the outputs, the system must drive the \overline{CE} and \overline{OE} pins to V_{IL}. \overline{CE} is the power control and selects the device. \overline{OE} is the output control and gates array data to the output pins. \overline{WE} should remain at V_{IH}.

The internal state machine is set for reading array data upon device power-up, or after a hardware reset. This ensures that no spurious alteration of the memory content occurs during the power transition. No command is necessary in this mode to obtain array data. Standard microprocessor read cycles that assert valid addresses on the device address inputs produce valid data on the device data outputs. The device remains enabled for read access until the command register contents are altered.

See Reading Array Data for more information. Refer to the AC Read Operations table for timing specifications and to the Read Operations Timings diagram for the timing waveforms. I_{CC1} in the DC Characteristics table represents the active current specification for reading array data.

Writing Commands/Command Sequences

To write a command or command sequence (which includes programming data to the device and erasing sectors of memory), the system must drive \overline{WE} and \overline{CE} to V_{IL}, and \overline{OE} to V_{IH}.

An erase operation can erase one sector, multiple sectors, or the entire device. The Sector Address Tables indicate the address space that each sector occupies. A Sector Address consists of the address bits required to uniquely select a sector. See the

Command Definitions section for details on erasing a sector or the entire chip, or suspending/resuming the erase operation.

After the system writes the autoselect command sequence, the device enters the autoselect mode. The system can then read autoselect codes from the internal register (which is separate from the memory array) on I/O7-I/O0⁹. Standard read cycle timings apply in this mode. Refer to the Autoselect Mode and Autoselect Command Sequence sections for more information.

I_{CC2} in the DC Characteristics table represents the active current specification for the write mode. The AC Characteristics section contains timing specification tables and timing diagrams for write operations.

Program and Erase Operation Status

During an erase or program operation, the system may check the status of the operation by reading the status bits on I/O7-I/O0⁹. Standard read cycle timings and I_{CC} read specifications apply. Refer to Write Operation Status for more information, and to each AC Characteristics section for timing diagrams.

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Standby Mode

When the system is not reading or writing to the device, it can place the device in the standby mode. In this mode, current consumption is greatly reduced, and the outputs are placed in the high impedance state, independent of the OE input.

The device enters the CMOS standby mode when CE and RESET pins are both held at VDD - 0.5 V. (Note that this is a more restricted voltage range than VIH.) The device enters the TTL standby mode when CE and RESET pins are both held at VIH. The device requires standard access time (tCE) for read access when the device is in either of these standby modes, before it is ready to read data.

The device also enters the standby mode when the RESET pin is driven low. Refer to the next section, RESET: Hardware Reset Pin .

If the device is deselected during erasure or programming, the device draws active current until the operation is completed.

In the DC Characteristics tables, ISB1 and ISB2 represent the standby current specification.

RESET: Hardware Reset Pin

The RESET pin provides a hardware method of resetting the device to reading array data. When the system drives the RESET pin low for at least a period of tRP, the device **immediately terminates** any operation in progress, tristates all data output pins, and ignores all read/write attempts for the duration of the

RESET pulse. The device also resets the internal state machine to reading array data. The operation that was interrupted should be reinitiated once the device is ready to accept another command sequence, to ensure data integrity.

Current is reduced for the duration of the RESET pulse. When RESET is held at VIL, the device enters the TTL standby mode; if RESET is held at VSS ± 0.5V, the device enters the CMOS standby mode.

The RESET pin may be tied to the system reset circuitry. A system reset would thus also reset the Flash memory, enabling the system to read the boot-up firmware from the Flash memory.

If RESET is asserted during a program or erase operation, the RY/BY pin remains a 0" (busy) until the internal reset operation is complete, which requires a time of tREADY (during Embedded Algorithms). The system can thus monitor RY/BY to determine whether the reset operation is complete. If RESET is asserted when a program or erase operation is not executing (RY/BY pin is 1"), the reset operation is completed within a time of tREADY (not during Embedded Algorithms). The system can read data tRH after the RESET pin returns to VIH .

Refer to the AC Characteristics tables for RESET parameters and timing diagram.

Output Disable Mode

When the OE input is at VIH, output from the device is disabled. The output pins are placed in the high impedance state.

Autoselect Mode

The autoselect mode provides manufacturer and device identification through identifier codes output on I/O7-I/O0⁹. This mode is primarily intended for programming equipment to automatically match a device to be programmed with its corresponding programming algorithm. However, the autoselect codes can also be accessed in-system through the command register.

When using programming equipment, the autoselect mode requires VID (11.5V to 12.5V) on address pin A9. Address pins A6, A1, and A0 must be as shown in Table 2, Autoselect Codes

(High Voltage Method). The Command Definitions , table 4, shows the remaining address bits that are don't care. When all necessary bits have been set as required, the programming equipment may then read the corresponding identifier code on I/O7-I/O0⁹.

To access the autoselect codes in-system, the host system can issue the autoselect command via the command register, as shown in the Command Definitions table. This method does not require VID. See Command Definitions for details on using the autoselect mode.

Table 2. Auto Select Codes (High Voltage Method)

Description	CE	OE	WE	A20-A18	A17-A10	A9	A8-A7	A6	A5-A2	A1	A0	I/O7-I/O0 ⁹
Manufacture ID	L	L	H	X	X	VID	X	VIL	X	VIL	VIL	01h
Device ID	L	L	H	X	X	VID	X	VIL	X	VIL	VIH	ADh

L = Logic Low = VIL, H = Logic High = VIH, SA = Sector Address, X = Don't Care.

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Table 3: SECTOR ADDRESS						
Sector	A20	A19	A18	A17	A16	Address Range
SA0	0	0	0	0	0	000000h-00FFFFh
SA1	0	0	0	0	1	010000h-01FFFFh
SA2	0	0	0	1	0	020000h-02FFFFh
SA3	0	0	0	1	1	030000h-03FFFFh
SA4	0	0	1	0	0	040000h-04FFFFh
SA5	0	0	1	0	1	050000h-05FFFFh
SA6	0	0	1	1	0	060000h-06FFFFh
SA7	0	0	1	1	1	070000h-07FFFFh
SA8	0	1	0	0	0	080000h-08FFFFh
SA9	0	1	0	0	1	090000h-09FFFFh
SA10	0	1	0	1	0	0A0000h-0AFFFFh
SA11	0	1	0	1	1	0B0000h-0BFFFFh
SA12	0	1	1	0	0	0C0000h-0CFFFFh
SA13	0	1	1	0	1	0D0000h-0DFFFFh
SA14	0	1	1	1	0	0E0000h-0EFFFFh
SA15	0	1	1	1	1	0F0000h-0FFFFFh
SA16	1	0	0	0	0	100000h-10FFFFh
SA17	1	0	0	0	1	110000h-11FFFFh
SA18	1	0	0	1	0	120000h-12FFFFh
SA19	1	0	0	1	1	130000h-13FFFFh
SA20	1	0	1	0	0	140000h-14FFFFh
SA21	1	0	1	0	1	150000h-15FFFFh
SA22	1	0	1	1	0	160000h-16FFFFh
SA23	1	0	1	1	1	170000h-17FFFFh
SA24	1	1	0	0	0	180000h-18FFFFh
SA25	1	1	0	0	1	190000h-19FFFFh
SA26	1	1	0	1	0	1A0000h-1AFFFFh
SA27	1	1	0	1	1	1B0000h-1BFFFFh
SA28	1	1	1	0	0	1C0000h-1CFFFFh
SA29	1	1	1	0	1	1D0000h-1DFFFFh
SA30	1	1	1	1	0	1E0000h-1EFFFFh
SA31	1	1	1	1	1	1F0000h-1FFFFFh

NOTE: All sectors are 64 Kbytes in size.

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Hardware Data Protection

The command sequence requirement of unlock cycles for programming or erasing provides data protection against inadvertent writes (refer to Table 3, Command Definitions). In addition, the following hardware data protection measures prevent accidental erasure or programming, which might otherwise be caused by spurious system level signals during V_{DD} power-up and power-down transitions, or from system noise.

Low V_{DD} Write Inhibit

When V_{DD} is less than V_{LKO} , the device does not accept any write cycles. This protects data during V_{DD} power-up and power-down. The command register and all internal program/erase circuits are disabled, and the device resets. Subsequent writes are ignored until V_{DD} is greater than V_{LKO} . The system must

provide the proper signals to the control pins to prevent unintentional writes when V_{DD} is greater than V_{LKO} .

Write Pulse Glitch Protection

Noise pulses of less than 5ns (typical) on \overline{OE} , \overline{CE} or \overline{WE} do not initiate a write cycle.

Logical Inhibit

Write cycles are inhibited by holding any one of $\overline{OE} = V_{IL}$, $\overline{CE} = V_{IH}$ or $\overline{WE} = V_{IH}$. To initiate a write cycle, \overline{CE} and \overline{WE} must be a logical zero while \overline{OE} is a logical one.

Power-Up Write Inhibit

If $\overline{WE} = \overline{CE} = V_{IL}$ and $\overline{OE} = V_{IH}$ during power up, the device does not accept commands on the rising edge of \overline{WE} . The internal state machine is automatically reset to reading array data on power-up.

COMMAND DEFINITIONS

Writing specific address and data commands or sequences into the command register initiates device operations. The Command Definitions table defines the valid register command sequences. Writing **incorrect address and data values** or writing them in the **improper sequence** resets the device to reading array data.

All addresses are latched on the falling edge of \overline{WE} or \overline{CE} , whichever happens later. All data is latched on the rising edge of \overline{WE} or \overline{CE} , whichever happens first. Refer to the appropriate timing diagrams in the AC Characteristics section.

Reading Array Data

The device is automatically set to reading array data after device power-up. No commands are required to retrieve data. The device is also ready to read array data after completing an Embedded Program or Embedded Erase algorithm.

After the device accepts an Erase Suspend command, the device enters the Erase Suspend mode. The system can read array data using the standard read timings, except that if it reads at an address within erase-suspended sectors, the device outputs status data. After completing a programming operation in the Erase Suspend mode, the system may once again read array data with the same exception. See Erase Suspend/Erased Resume Commands for more information on this mode.

The system *must* issue the reset command to re-enable the device for reading array data if $I/O5^9$ goes high, or while in the autoselect mode. See the Reset Command section, next.

See also Requirements for Reading Array Data in the Device Bus Operations section for more information. The Read Operations table provides the read parameters, and Read Operation Timings diagram shows the timing diagram.

Reset Command

Writing the reset command to the device resets the device to reading array data. Address bits are don't care for this command.

The reset command may be written between the sequence cycles in an erase command sequence before erasing begins. This resets the device to reading array data. Once erasure begins, however, the device ignores reset commands until the operation is complete.

The reset command may be written between the sequence cycles in a program command sequence before programming begins. This resets the device to reading array data (also applies to programming in Erase Suspend mode). Once programming begins, however, the device ignores reset commands until the operation is complete.

The reset command may be written between the sequence cycles in an autoselect command sequence. Once in the autoselect mode, the reset command *must* be written to return to reading array data (also applies to autoselect during Erase Suspend).

If $I/O5^9$ goes high during a program or erase operation, writing the reset command returns the device to reading array data (also applies during Erase Suspend).

Autoselect Command Sequence

The autoselect command sequence allows the host system to access the manufacturer and device codes, and determine whether or not a sector is protected. The Command Definitions table shows the address and data requirements. This method is an alternative to that shown in Table 2, Autoselect Codes (High Voltage Method), which is intended for PROM programmers and requires V_{ID} on address bit A9.

The autoselect command sequence is initiated by writing two unlock cycles, followed by the autoselect command. The device then enters the autoselect mode, and the system may read at any address any number of times, without initiating another command sequence.

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A read cycle at address XX00h retrieves the manufacturer code. A read cycle at address XX01h returns the device code. A read cycle containing a sector address (SA) and the address 02h in returns 01h if that sector is protected, or 00h if it is unprotected. Refer to the Sector Address tables for valid sector addresses.

The system must write the reset command to exit the autoselect mode and return to reading array data.

Byte Program Command Sequence

Programming is a four-bus-cycle operation. The program command sequence is initiated by writing two unlock write cycles, followed by the program set-up command. The program address and data are written next, which in turn initiate the Embedded Program algorithm. The system is not required to provide further controls or timings. The device automatically provides internally generated program pulses and verify the programmed cell margin. The Command Definitions table shows the address and data requirements for the byte program command sequence.

When the Embedded Program algorithm is complete, the device then returns to reading array data and addresses are no longer latched. The system can determine the status of the program operation by using I/O7⁹, I/O6⁹, or RY/BY. See Write Operation Status for information on these status bits.

Any commands written to the device during the Embedded Program Algorithm are ignored. Note that a **hardware reset** immediately terminates the programming operation. The program command sequence should be reinitiated once the device has reset to reading array data, to ensure data integrity.

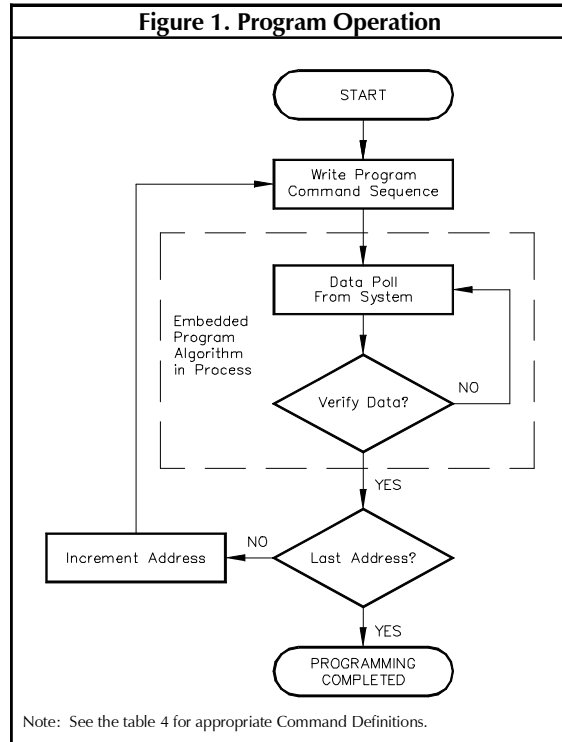
Programming is allowed in any sequence and across sector boundaries. **A bit cannot be programmed from a 0" back to a 1".** Attempting to do so may halt the operation and set I/O5⁹ to 1, or cause the Data Polling algorithm to indicate the operation was successful. However, a succeeding read will show that the data is still 0". Only erase operations can convert a 0" to a 1".

Chip Erase Command Sequence

Chip erase is a six-bus-cycle operation. The chip erase command sequence is initiated by writing two unlock cycles, followed by a set-up command. Two additional unlock write cycles are then followed by the chip erase command, which in turn invokes the Embedded Erase algorithm. The device does *not* require the system to preprogram prior to erase. The Embedded Erase algorithm automatically preprograms and verifies the entire memory for an all zero data pattern prior to electrical erase. The system is not required to provide any controls or timings during these operations. The Command Definitions table shows the address and data requirements for the chip erase command sequence.

Any commands written to the chip during the Embedded Erase algorithm are ignored. Note that a **hardware reset** during the chip erase operation immediately terminates the operation. The Chip Erase command sequence should be reinitiated once the device has returned to reading array data, to ensure data integrity.

The system can determine the status of the erase operation by using I/O7⁹, I/O6⁹, I/O2⁹, or RY/BY. See Write Operation



Status for information on these status bits. When the Embedded Erase algorithm is complete, the device returns to reading array data and addresses are no longer latched.

Figure 2 illustrates the algorithm for the erase operation. See the Erase/Program Operations tables in AC Characteristics for parameters, and to the Chip/Sector Erase Operation Timings for timing waveforms.

Sector Erase Command Sequence

Sector erase is a six bus cycle operation. The sector erase command sequence is initiated by writing two unlock cycles, followed by a set-up command. Two additional unlock write cycles are then followed by the address of the sector to be erased, and the sector erase command. The Command Definitions table shows the address and data requirements for the sector erase command sequence.

The device does *not* require the system to preprogram the memory prior to erase. The Embedded Erase algorithm automatically programs and verifies the sector for an all zero data pattern prior to electrical erase. The system is not required to provide any controls or timings during these operations.

After the command sequence is written, a sector erase time-out of 50µs begins. During the time-out period, additional sector addresses and sector erase commands may be written. Loading the sector erase buffer may be done in any sequence, and the

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number of sectors may be from one sector to all sectors. The time between these additional cycles must be less than 50µs, otherwise the last address and command might not be accepted, and erasure may begin. It is recommended that processor interrupts be disabled during this time to ensure all commands are accepted. The interrupts can be re-enabled after the last Sector Erase command is written. If the time between additional sector erase commands can be assumed to be less than 50s, the system need not monitor I/O3⁹. **Any command other than Sector Erase or Erase Suspend during the time-out period resets the device to reading array data.** The system must rewrite the command sequence and any additional sector addresses and commands.

The system can monitor I/O3⁹ to determine if the sector erase timer has timed out. (See the I/O3: Sector Erase Timer section.) The time-out begins from the rising edge of the final WE pulse in the command sequence.

Once the sector erase operation has begun, only the Erase Suspend command is valid. All other commands are ignored. Note that a **hardware reset** during the sector erase operation immediately terminates the operation. The Sector Erase command sequence should be reinitiated once the device has returned to reading array data, to ensure data integrity.

When the Embedded Erase algorithm is complete, the device returns to reading array data and addresses are no longer latched. The system can determine the status of the erase operation by using I/O7⁹, I/O6⁹, I/O2⁹, or RY/BY. Refer to Write Operation Status for information on these status bits.

Figure 2 illustrates the algorithm for the erase operation. Refer to the Erase/Program Operations tables in the AC Characteristics section for parameters, and to the Sector Erase Operations Timing diagram for timing waveforms.

Erase Suspend/Erase Resume Commands

The Erase Suspend command allows the system to interrupt a sector erase operation and then read data from, or program data to, any sector not selected for erasure. This command is valid only during the sector erase operation, including the 50µs time-out period during the sector erase command sequence. The Erase Suspend command is ignored if written during the chip erase operation or Embedded Program algorithm. Writing the Erase Suspend command during the Sector Erase time-out immediately terminates the time-out period and suspends the erase operation. Addresses are don't-cares when writing the Erase Suspend command.

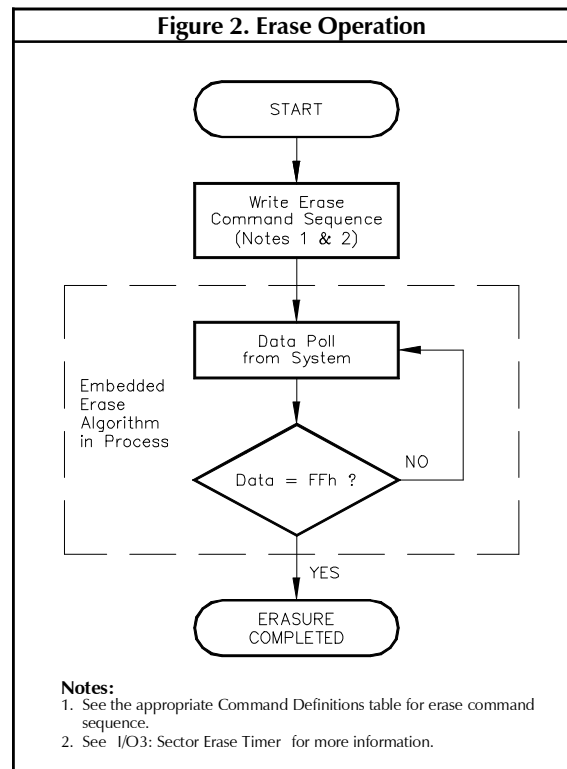
When the Erase Suspend command is written during a sector erase operation, the device requires a maximum of 20µs to suspend the erase operation. However, when the Erase Suspend command is written during the sector erase time-out, the device immediately terminates the time-out period and suspends the erase operation.

After the erase operation has been suspended, the system can read array data from or program data to any sector not selected for erasure. (The device Erase Suspends all sectors selected for erasure.) Normal read and write timings and command

definitions apply. Reading at any address within erase-suspended sectors produces status data on I/O7-I/O0⁹. The system can use I/O7⁹, or I/O6⁹ and I/O2⁹ together, to determine if a sector is actively erasing or is erase-suspended. See Write Operation Status for information on these status bits.

After an erase-suspended program operation is complete, the system can once again read array data within non-suspended sectors. The system can determine the status of the program operation using the I/O7⁹ or I/O6⁹ status bits, just as in the standard program operation. See Write Operation Status for more information. The system may also write the autoselect command sequence when the device is in the Erase Suspend mode. The device allows reading autoselect codes even at addresses within erasing sectors, since the codes are not stored in the memory array. When the device exits the autoselect mode, the device reverts to the Erase Suspend mode, and is ready for another valid operation. See Autoselect Command Sequence for more information.

The system must write the Erase Resume command (address bits are don't care) to exit the erase suspend mode and continue the sector erase operation. Further writes of the Resume command are ignored. Another Erase Suspend command can be written after the device has resumed erasing.



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Command Sequence ¹	Cycles	Bus Cycles ^{2, 3 & 4}											
		First		Second		Third		Forth		Fifth		Sixth	
		Address	Data	Address	Data	Address	Data	Address	Data	Address	Data	Address	Data
Read ⁵	1	RA	F0	-	-	-	-	-	-	-	-	-	-
Reset ⁶	1	XXX	F0	-	-	-	-	-	-	-	-	-	-
Autoselect ⁷	Manufacturer ID	4	555	AA	2AA	55	555	90	X00	01	-	-	-
	Device ID	4	555	AA	2AA	55	555	90	X01	AD	-	-	-
Program	4	555	AA	2AA	55	555	A0	PA	PD	-	-	-	-
Chip Erase	6	555	AA	2AA	55	555	80	555	AA	2AA	55	555	10
Sector Erase	6	555	AA	2AA	55	555	8	555	AA	2AA	55	SA	30
Erase Suspend ⁹	1	XXX	B0	-	-	-	-	-	-	-	-	-	-
Ease Resume ¹⁰	1	XXX	30	-	-	-	-	-	-	-	-	-	-

Legend:

- X = Don't Care
- RA = Address of the memory location to be read.
- RD = Data read from location RA during read operation.
- PA = Address of the memory location to be programmed.
Addresses latch on the falling edge of the WE or CE pulse, whichever happens later.
- PD = Data to be programmed at location PA. Data latches on the rising edge of WE or CE pulse, whichever happens first.
- SA = Address of the sector to be verified (in autoselect mode) or erased.
Address bits A20 - A16 select a unique sector.
- SGA = Address of the sector group to be verified. Address bits A20 - A18 select a unique sector group.

Command Definition Notes:

1. See Table 1 for description of bus operations.
2. All values are in hexadecimal.
3. Except when reading array or autoselect data, all bus cycles are write operations.
4. Address bits A20 - A11 are don't cares for unlock and command cycles, unless SA or PA required.
5. No unlock or command cycles required when reading array data.
6. The Reset command is required to return to reading array data when device is in the autoselect mode, or if I/O5⁹ goes high (while the device is providing status data).
7. The fourth cycle of the autoselect command sequence is a read cycle.
8. The data is 00h for an unprotected sector group and 01h for a protected sector group. See Autoselect Command Sequence for more information.
9. The system may read and program in non-erasing sectors, or enter the autoselect mode, when in the Erase Suspend mode. The Erase Suspend command is valid only during a sector erase operation.
10. The Erase Resume command is valid only during the Erase Suspend mode.

WRITE OPERATION STATUS

The device provides several bits to determine the status of a write operation: $I/O2^9$, $I/O3^9$, $I/O5^9$, $I/O6^9$, $I/O7^9$, and RY/\overline{BY} . Table 5 and the following subsections describe the functions of these bits. $I/O7^9$, RY/\overline{BY} , and $I/O6^9$ each offer a method for determining whether a program or erase operation is complete or in progress. These three bits are discussed first.

$I/O7^9$: \overline{Data} Polling

The \overline{Data} Polling bit, $I/O7^9$, indicates to the host system whether an Embedded Algorithm is in progress or completed, or whether the device is in Erase Suspend. \overline{Data} Polling is valid after the rising edge of the final \overline{WE} pulse in the program or erase command sequence.

During the Embedded Program algorithm, the device outputs on $I/O7^9$ the complement of the datum programmed to $I/O7^9$. This $I/O7^9$ status also applies to programming during Erase Suspend. When the Embedded Program algorithm is complete, the device outputs the datum programmed to $I/O7^9$. The system must provide the program address to read valid status information on $I/O7^9$. If a program address falls within a protected sector, \overline{Data} Polling on $I/O7^9$ is active for approximately $2\mu s$, then the device returns to reading array data.

During the Embedded Erase algorithm, \overline{Data} Polling produces a 0" on $I/O7^9$. When the Embedded Erase algorithm is complete, or if the device enters the Erase Suspend mode, \overline{Data} Polling produces a 1" on $I/O7^9$. This is analogous to the complement/true datum output described for the Embedded Program algorithm: the erase function changes all the bits in a sector to 1"; prior to this, the device outputs the complement, or 0". The system must provide an address within any of the sectors selected for erasure to read valid status information on $I/O7^9$.

After an erase command sequence is written, if all sectors selected for erasing are protected, \overline{Data} Polling on $I/O7^9$ is active for approximately $100\mu s$, then the device returns to reading array data. If not all selected sectors are protected, the Embedded Erase algorithm erases the unprotected sectors, and ignores the selected sectors that are protected.

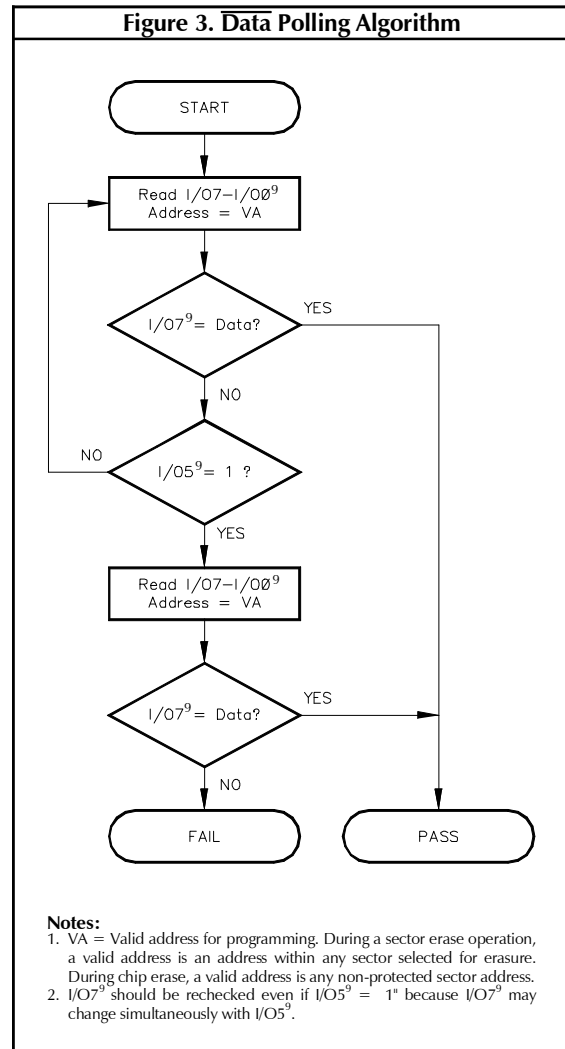
When the system detects $I/O7^9$ has changed from the complement to true data, it can read valid data at $I/O7-I/O0^9$ on the following read cycles. This is because $I/O7^9$ may change asynchronously with $I/O0 - I/O6^9$ while Output Enable (\overline{OE}) is asserted low. The \overline{Data} Polling Timings (During Embedded Algorithms) in the AC Characteristics section illustrates this.

Table 5 shows the outputs for \overline{Data} Polling on $I/O7^9$. Figure 3 shows the \overline{Data} Polling algorithm.

RY/\overline{BY} : Ready/Busy

The RY/\overline{BY} is a dedicated, open-drain output pin that indicates whether an Embedded Algorithm is in progress or complete. The RY/\overline{BY} status is valid after the rising edge of the final \overline{WE} pulse in the command sequence. Since RY/\overline{BY} is an open-drain output, several RY/\overline{BY} pins can be tied together in parallel with a pull-up resistor to V_{DD} .

If the output is low (Busy), the device is actively erasing or programming. (This includes programming in the Erase Suspend



mode.) If the output is high (Ready), the device is ready to read array data (including during the Erase Suspend mode), or is in the standby mode.

Table 6 shows the outputs for RY/\overline{BY} . The timing diagrams for read, reset, program, and erase shows the relationship of RY/\overline{BY} to other signals.

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Table 5. Write Operation Status

Operation		I/O7 ^{1,3}	I/O6 ³	I/O5 ^{2,3}	I/O3 ³	I/O2 ³	RY/BY
Standard Mode	Embedded Program Algorithm	I/O7	Toggle	0	N/A	No Toggle	0
	Embedded Erase Algorithm	0	Toggle	0	1	Toggle	0
Erase Suspend Mode	Read within Erase Suspended Sector	1	No Toggle	0	N/A	Toggle	1
	Read within Non-Erase Suspended Sector	Data	Data	Data	Data	Data	1
	Erase-Suspend-Program	I/O7	Toggle	0	N/A	N/A	0

Notes:

1. I/O7⁹ and I/O2⁹ require a valid address when reading status information. Refer to the appropriate subsection for further details.
2. I/O5⁹ switches to 1 when an Embedded Program or Embedded Erase operation has exceeded the maximum timing limits. See I/O5: Exceeded Timing Limits for more information.
3. Data Polling Bits = I/O7, I/O15
Toggle Bits I = I/O6, I/O14
Exceeding Timing Limits Bits = I/O5, I/O13
Sector Erase Timer Bits = I/O3, I/O11
Toggle Bits II = I/O2, I/O10

I/O6: Toggle Bit I

Toggle Bit I on I/O6⁹ indicates whether an Embedded Program or Erase algorithm is in progress or complete, or whether the device has entered the Erase Suspend mode. Toggle Bit I may be read at any address, and is valid after the rising edge of the final WE pulse in the command sequence (prior to the program or erase operation), and during the sector erase time-out.

During an Embedded Program or Erase algorithm operation, successive read cycles to any address cause I/O6⁹ to toggle. (The system may use either OE or CE to control the read cycles.) When the operation is complete, I/O6⁹ stops toggling.

After an erase command sequence is written, if all sectors selected for erasing are protected, I/O6⁹ toggles for approximately 100μs, then returns to reading array data. If not all selected sectors are protected, the Embedded Erase algorithm erases the unprotected sectors, and ignores the selected sectors that are protected.

The system can use I/O6⁹ and I/O2⁹ together to determine whether a sector is actively erasing or is erase-suspended. When the device is actively erasing (that is, the Embedded Erase algorithm is in progress), I/O6⁹ toggles. When the device enters the Erase Suspend mode, I/O6 stops toggling. However, the system must also use I/O2⁹ to determine which sectors are erasing or erase-suspended. Alternatively, the system can use I/O7⁹ (see the subsection on I/O7: Data Polling).

If a program address falls within a protected sector, I/O6⁹ toggles for approximately 2μs after the program command sequence is written, then returns to reading array data.

I/O6⁹ also toggles during the erase-suspend-program mode, and stops toggling once the Embedded Program algorithm is complete.

The Write Operation Status table shows the outputs for Toggle Bit I on I/O6⁹. Refer to Figure 4 for the toggle bit algorithm, and to the Toggle Bit Timings in the AC Characteristics section for the timing diagram. The I/O2⁹ vs. I/O6⁹ figure shows the differences between I/O2 and I/O6 in graphical form. See also the subsection on I/O2: Toggle Bit II.

I/O2: Toggle Bit II

The Toggle Bit II on I/O2⁹, when used with I/O6⁹, indicates whether a particular sector is actively erasing (that is, the Embedded Erase algorithm is in progress), or whether that sector is erase-suspended. Toggle Bit II is valid after the rising edge of the final WE pulse in the command sequence.

I/O2⁹ toggles when the system reads at addresses within those sectors that have been selected for erasure. (The system may use either OE or CE to control the read cycles.) But I/O2⁹ cannot distinguish whether the sector is actively erasing or is erase-suspended. I/O6⁹, by comparison, indicates whether the device is actively erasing, or is in Erase Suspend, but cannot distinguish which sectors are selected for erasure. Thus, both status bits are required for sector and mode information. Refer to Table 6 to compare outputs for I/O2⁹ and I/O6⁹.

Figure 4 shows the toggle bit algorithm in flowchart form, and the section I/O2: Toggle Bit II explains the algorithm. See also the I/O6: Toggle Bit I subsection. Refer to the Toggle Bit Timings figure for the toggle bit timing diagram. The I/O2⁹ vs. I/O6⁹ figure shows the differences between I/O2⁹ and I/O6⁹ in graphical form.

Reading Toggle Bits I/O6-I/O2

Refer to Figure 4 for the following discussion. Whenever the system initially begins reading toggle bit status, it must read I/O7-I/O0⁹ at least twice in a row to determine whether a toggle bit

is toggling. Typically, a system would note and store the value of the toggle bit after the first read. After the second read, the system would compare the new value of the toggle bit with the first. If the toggle bit is not toggling, the device has completed the program or erase operation. The system can read array data on I/O7- I/O0⁹ on the following read cycle.

However, if after the initial two read cycles, the system determines that the toggle bit is still toggling, the system also should note whether the value of I/O5⁹ is high (see the section on I/O5). If it is, the system should then determine again whether the toggle bit is toggling, since the toggle bit may have stopped toggling just as I/O5⁹ went high. If the toggle bit is no longer toggling, the device has successfully completed the program or erase operation. If it is still toggling, the device did not complete the operation successfully, and the system must write the reset command to return to reading array data.

The remaining scenario is that the system initially determines that the toggle bit is toggling and I/O5⁹ has not gone high. The system may continue to monitor the toggle bit and I/O5⁹ through successive read cycles, determining the status as described in the previous paragraph. Alternatively, it may choose to perform other system tasks. In this case, the system must start at the beginning of the algorithm when it returns to determine the status of the operation (top of Figure 4).

I/O5: Exceeded Timing Limits

I/O5⁹ indicates whether the program or erase time has exceeded a specified internal pulse count limit. Under these conditions I/O5⁹ produces a 1". This is a failure condition that indicates the program or erase cycle was not successfully completed.

The I/O5⁹ failure condition may appear if the system tries to program a 1" to a location that is previously programmed to 0.

Only an erase operation can change a 0" back to a 1". Under this condition, the device halts the operation, and when the operation has exceeded the timing limits, I/O5⁹ produces a 1".

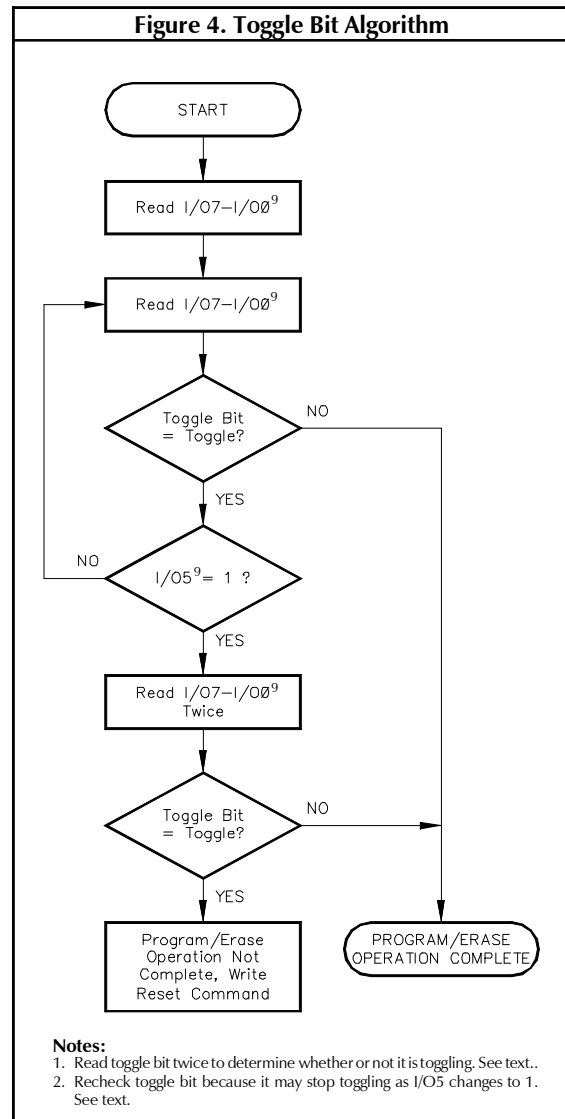
Under both these conditions, the system must issue the reset command to return the device to reading array data.

I/O3: Sector Erase Timer

After writing a sector erase command sequence, the system may read I/O3⁹ to determine whether or not an erase operation has begun. (The sector erase timer does not apply to the chip erase command.) If additional sectors are selected for erasure, the entire time-out also applies after each additional sector erase command. When the time-out is complete, I/O3⁹ switches from 0" to 1". The system may ignore I/O3⁹ if the system can guarantee that the time between additional sector erase commands will always be less than 50µs. See also the Sector Erase Command Sequence section.

After the sector erase command sequence is written, the system should read the status on I/O7⁹ (Data Polling) or I/O6⁹ (Toggle Bit I) to ensure the device has accepted the command sequence, and then read I/O3⁹. If I/O3⁹ is 1", the internally controlled erase cycle has begun; all further commands (other than Erase

Suspend) are ignored until the erase operation is complete. If I/O3⁹ is 0", the device will accept additional sector erase commands. To ensure the command has been accepted, the system software should check the status of I/O3⁹ prior to and following each subsequent sector erase command. If I/O3⁹ is high on the second status check, the last command might not have been accepted. Table 5 shows the outputs for I/O3⁹.



PRELIMINARY

RECOMMENDED OPERATING RANGE ¹						
Symbol	Characteristic	Min.	Typ.	Max.	Unit	
V _{DD}	Supply Voltage	4.5	5.0	5.5	V	
V _{IH}	Input HIGH Voltage	2.2		V _{DD} +0.5	V	
V _{IL}	Input LOW Voltage	-0.5 ²		0.8	V	
T _A	Operating Temperature	C	0	+25	+70	°C
		I	-40	+25	+85	
		M/B	-55	+25	+125	

ABSOLUTE MAXIMUM RATING			
Symbol	Parameter	Max.	Unit
T _{STC}	Storage Temperature	-65 to +150	°C
T _{BIAS}	Temperature Under Bias	-55 to +150	°C
T _{OP}	Operating Temperature	-55 to +150	°C
I _{OUT}	Output Short Circuit Current	200 ⁴	mA
V _{DD}	Supply Voltage ²	-0.5 to +7.0 ³	V
V _{IO}	Input/Output Voltage A9, OE, RESET ³	-0.5 to +12.5	V
	Input Voltage All Other Pins ²	-0.5 to +7.0	

CAPACITANCE ⁶ : T _A = 25°C, F = 1.0MHz				
Symbol	Parameter	Max.	Unit	Condition
C _{ADR}	Address Input	20	pF	V _{IN} = 0V
C _{CE}	Chip Enable	15		
C _{WE}	Write Enable	25		
C _{OE}	Output Enable	35		
C _{I/O}	Data Input/Output	20		

DC OUTPUT CHARACTERISTICS					
Symbol	Parameter	Condition	Min.	Max.	Unit
V _{OH}	HIGH Voltage	I _{OH} = 2.5mA	2.4		V
V _{OL}	LOW Voltage	I _{OL} = 12mA		0.45	V

DC OPERATING CHARACTERISTICS: Over Operating Ranges						
Symbol	Characteristics	Test Condition	Min.	Typ.	Max.	Unit
I _{LI}	Input Load Current	V _{IN} = V _{SS} to V _{DD} , V _{DD} = V _{DD} Max.			±2.0	μA
I _{LIT}	A9 Input Load Current	V _{DD} = V _{DD} Max., A9 = 12.5V			100	μA
I _{OUT}	Output Leakage Current	V _{OUT} = V _{SS} to V _{DD} , V _{DD} = V _{DD} Max.			±1.0	μA
I _{CC1}	V _{DD} Read Current ⁷	$\overline{CE} = V_{IL}$, $\overline{OE} = V_{IH}$		50	80	mA
I _{CC2}	V _{DD} Write Current ^{6,8}	$\overline{CE} = V_{IL}$, $\overline{CE} = V_{IH}$		50	120	mA
I _{SB1}	Standby Current (TTL)	V _{DD} = V _{DD} Max., $\overline{CE} = V_{IH}$, RESET = V _{IH} or RESET = V _{IH}		0.8	2.0	mA
I _{SB2}	V _{DD} Standby Current (CMOS)	V _{DD} = V _{DD} Max., $\overline{CE} = V_{DD} \pm 0.5V$, or RESET = V _{DD} ± 0.5V or RESET = V _{SS} ± 0.5V		2	10	μA
V _{IL}	Input LOW Voltage		-0.5		0.8	V
V _{IH}	Input HIGH Voltage		2.0		V _{DD} + 0.5	V
V _{ID}	Voltage for Autoselect and Sector Protect	V _{DD} = 5.0V	11.5		12.5	V
V _{OL}	Output LOW Voltage	I _{OL} = 12mA, V _{DD} = V _{DD} Max.			0.45	V
V _{OH}	Output HIGH Voltage	I _{OH} = -2.5mA, V _{DD} = V _{DD} Max.	2.4			V
V _{LKO}	Low V _{DD} Lock-out Voltage		3.2		4.2	V

PRELIMINARY

ERASE AND PROGRAMMING PERFORMANCE				
Parameter	Typ. ¹	Max. ²	Unit	Comments
Sector Erase Time	1	8	sec	Excludes 00h programming prior to erasure. ⁴
Chip Erase Time	32	256	sec	
Byte Programming Time	7	300	μs	Excludes system-level overhead. ⁵
Chip Programming Time ³	14.4	43.2	sec	

Notes:

1. Typical program and erase times assume the following conditions: 25°C, 5.0V V_{DD}, 1,000,000 cycles. Additionally, programming typicals assume checkerboard pattern.
2. Under worst case conditions of 90°C, V_{DD} = 4.5 V, 1,000,000 cycles.
3. The typical chip programming time is considerably less than the maximum chip programming time listed, since most bytes program faster than the maximum byte program time listed. If the maximum byte program time given is exceeded, only then does the device set I/O5⁹ = 1. See the section on I/O5⁹ for further information.
4. In the pre-programming step of the Embedded Erase algorithm, all bytes are programmed to 00h before erasure.
5. System-level overhead is the time required to execute the four-bus-cycle sequence for programming. See Table 5 for further information on command definitions.
6. The device has a guaranteed minimum erase and program cycle endurance of 1,000,000 cycles.

LATCHUP CHARACTERISTICS			
Parameter	Min.	Max.	Unit
Input Voltage with Respect to V _{SS} on I/O Pins	-1.0	V _{DD} + 1.0	V
V _{DD} Current	-100	+100	mA

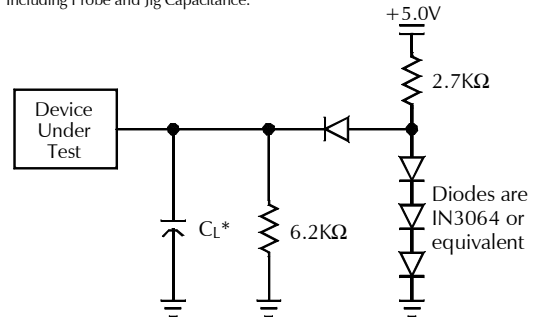
Note: Includes all pins except V_{DD}. Test Conditions: V_{DD} = 5.0V, one pin at a time.

DATA RETENTION			
Parameter	Condition	Max.	Unit
Minimum Pattern Data Retention	+150°C	10	Years
	+125°C	20	Years

Test Specifications		
Test Conditions	All Speed Options	Unit
Output	1 TTL Gate	
Output Load Capacitance, C _L *	100	pF
Input Rinse and Fall Times	20	ns
Input Pulse Levels	0.45 - 2.4	V
Input Timing Measurement Reference Levels	0.8	V
Output Timing Measurement Reference Levels	2.0	V

Figure 6. Output Load Test Conditions

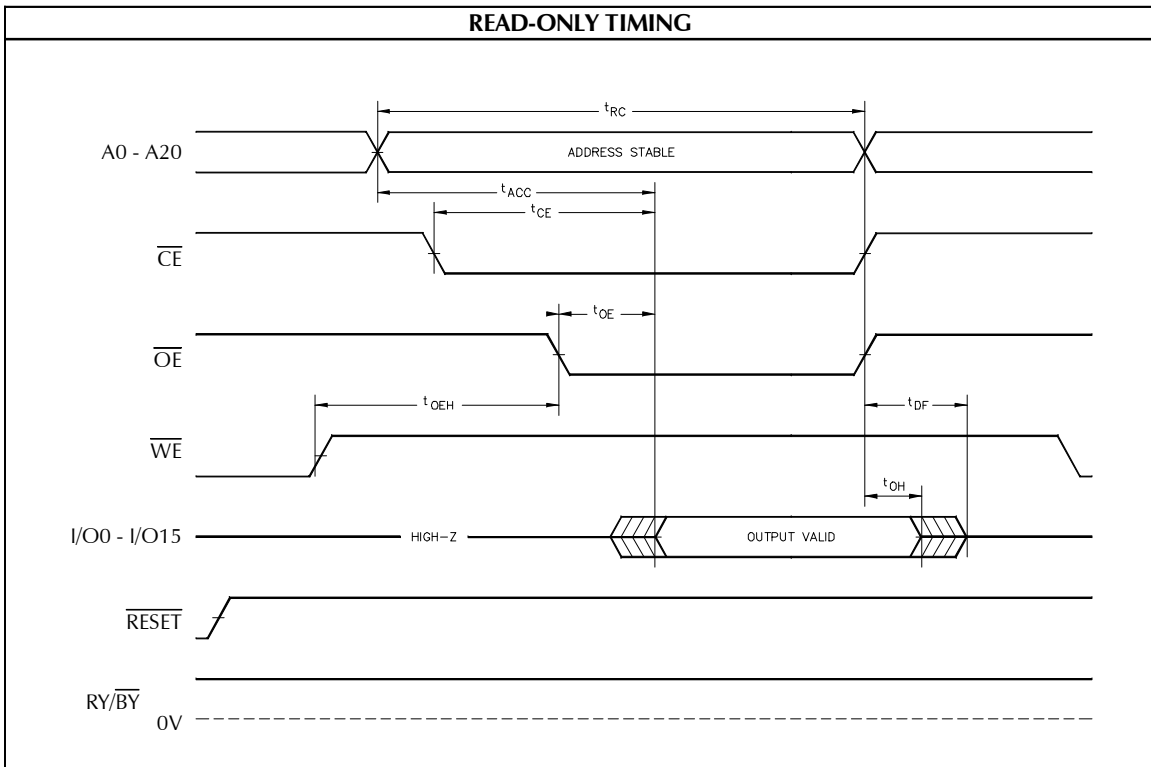
* Including Probe and Jig Capacitance.



PRELIMINARY

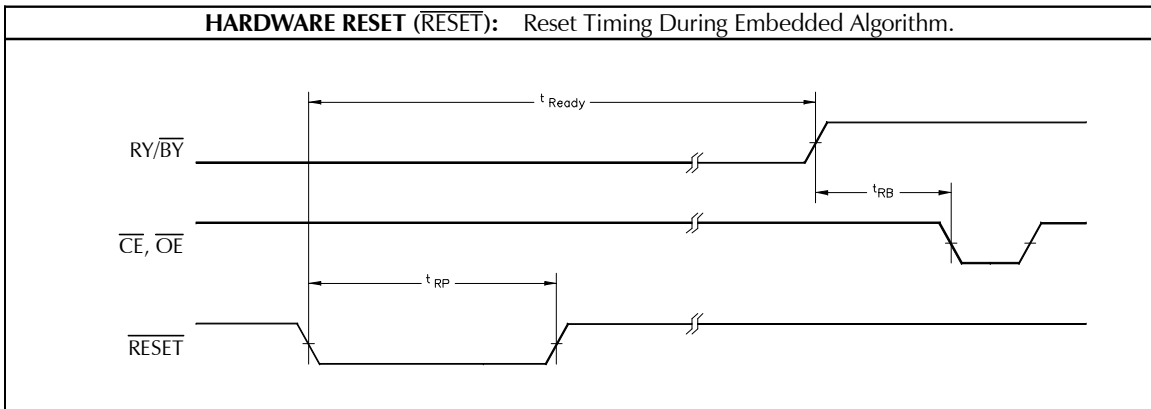
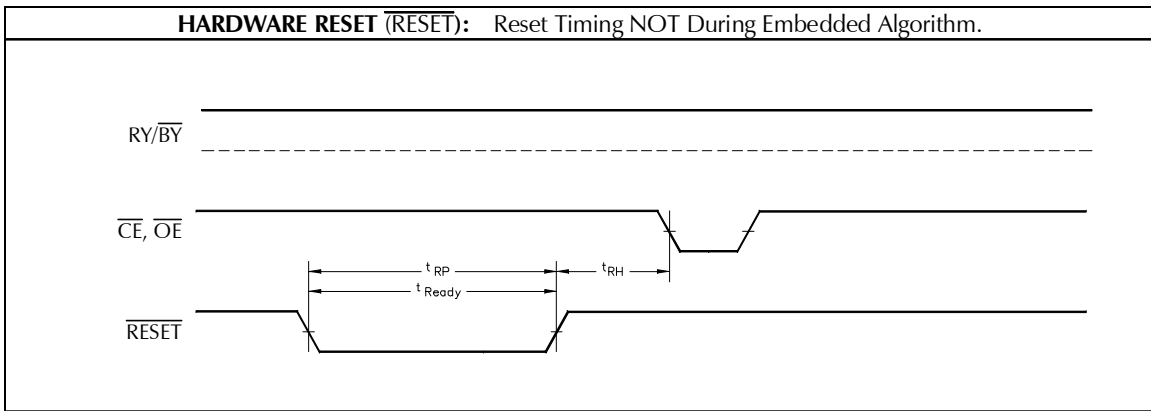
AC OPERATING CONDITIONS AND CHARACTERISTICS - Read-Only Operations											
No.	Symbol	Parameter	70ns*		90ns		120ns		150ns		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
1	t_{RC}	Read Cycle Time ⁶	70		90		120		150		ns
2	t_{ACC}	Address to Output Delay		70		90		120		150	ns
3	t_{CE}	Chip Enable to Output Delay		70		90		120		150	ns
4	t_{OE}	Chip Enable to Output Delay		40		40		50		55	ns
5	t_{OEh}	Output Enable Hold Time ⁶	Read		0		0		0		ns
		Toggle and Data Polling		10		10		10		10	
6	t_{DF}	Chip Enable to Output in HIGH-Z ⁶		20		20		30		35	ns
7	t_{DF}	Output Enable to Output in HIGH-Z ⁶		20		20		30		35	ns
8	t_{OH}	Output Hold Time from Addresses \overline{CE} or \overline{OE} Whichever Occurs First	0		0		0		0		ns
9	t_{READY}	\overline{RESET} Pin Low to Read Mode ⁶		20		20		20		20	μ s

* $V_{DD} = 5.0V \pm 5\%$.



PRELIMINARY

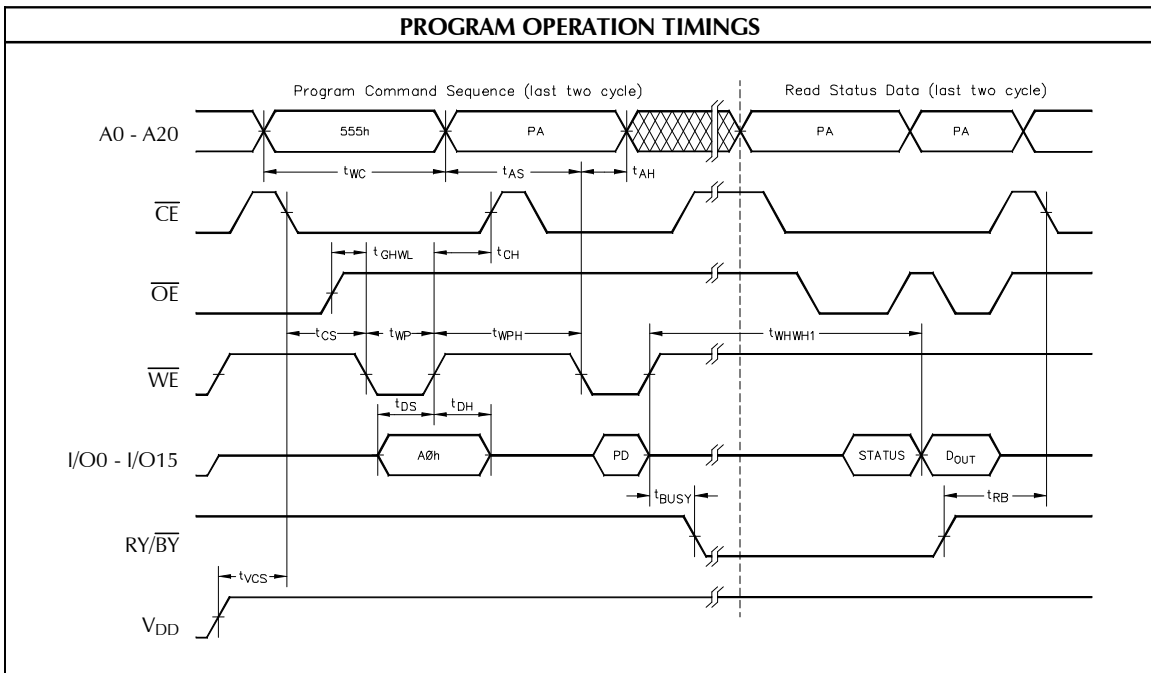
AC OPERATING CONDITIONS AND CHARACTERISTICS - HARDWARE RESET ($\overline{\text{RESET}}$)					
No.	Symbol	Parameter	Min.	Max.	Unit
10	t_{READY}	$\overline{\text{RESET}}$ Pin Low (During Embedded Algorithms) to Read or Write ⁶		20	μs
11	t_{READY}	$\overline{\text{RESET}}$ Pin Low (NOT During Embedded Algorithms) to Read or Write ⁶		500	ns
12	t_{RP}	$\overline{\text{RESET}}$ Pulse Width	500		ns
13	t_{RH}	$\overline{\text{RESET}}$ High Time before Read ⁶	50		ns
14	t_{RB}	RY/ $\overline{\text{BY}}$ Recovery Time	0		ns



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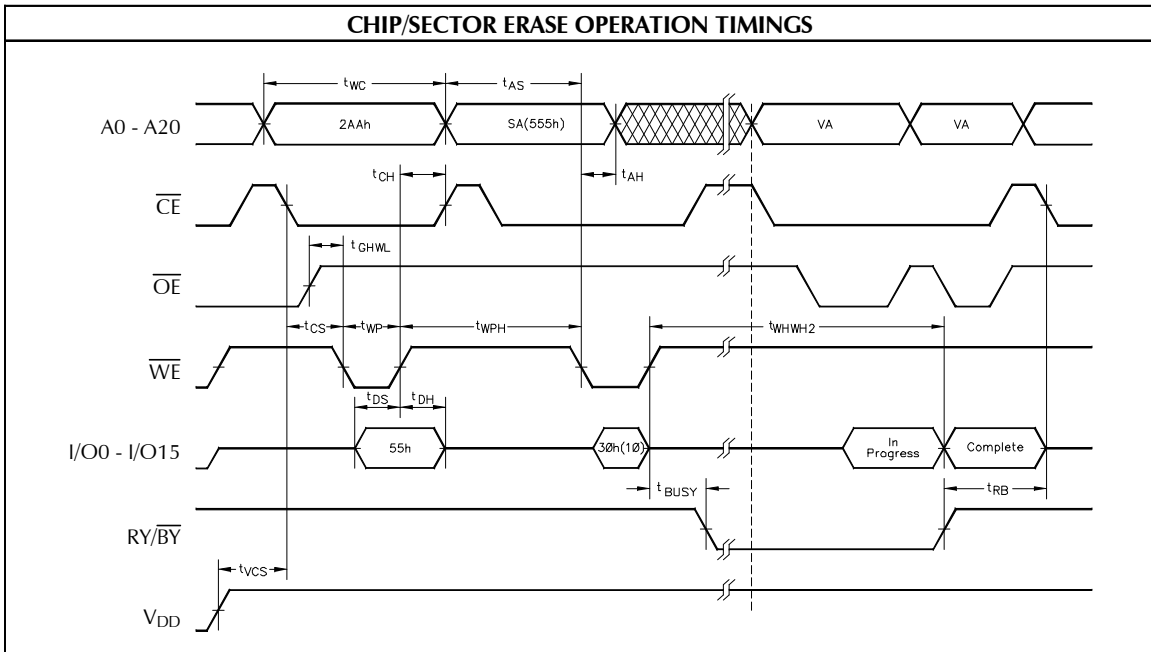
AC OPERATING CONDITIONS AND CHARACTERISTICS - ERASE/PROGRAM OPERATION															
No.	Symbol	Parameter	70ns*			90ns			120ns			150ns			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
15	t _{WC}	Write Cycle Time ⁶	70			90			120			150			ns
16	t _{AS}	Address Set-up Time	0			0			0			0			ns
17	t _{AH}	Address Hold Time	40			45			50			50			ns
18	t _{DS}	Data Setup Time	40			45			50			50			ns
19	t _{DH}	Data Hold Time	0			0			0			0			ns
20	t _{OES}	Output Enable Setup Time	0			0			0			0			ns
21	t _{GHWL}	Read Recover Time before Write (OE High to WE Low)	0			0			0			0			ns
22	t _{CS}	Chip Enable Setup Time	0			0			0			0			ns
23	t _{CH}	Chip Enable Hold Time	0			0			0			0			ns
24	t _{WP}	Write Pulse Width	40			45			50			50			ns
25	t _{WPH}	Write Pulse Width High	20			20			20			20			ns
26	t _{WHWH1}	Byte Programming Operation		7			7			7			7		μs
27	t _{WHWH2}	Sector Erase Operation		1	8		1	8		1	8		1	8	sec
28	t _{VCS}	V _{DD} setup Time ⁶	50			50			50			50			μs
29	t _{BUSY}	Write Enable to RY/ $\overline{\text{BY}}$ Valid	40			40			40			40			ns

* V_{DD} = 5.0V ± 5%.

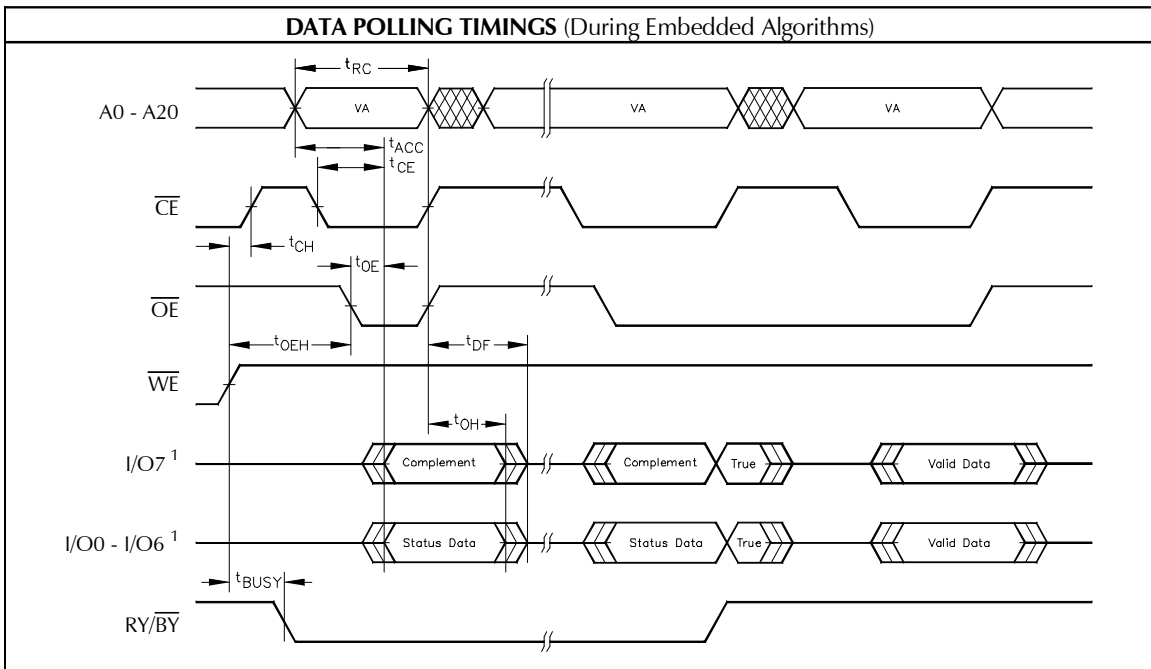


NOTE: PA = Program Address, PD = Program Data, D_{OUT} is the true data at the program address.

PRELIMINARY

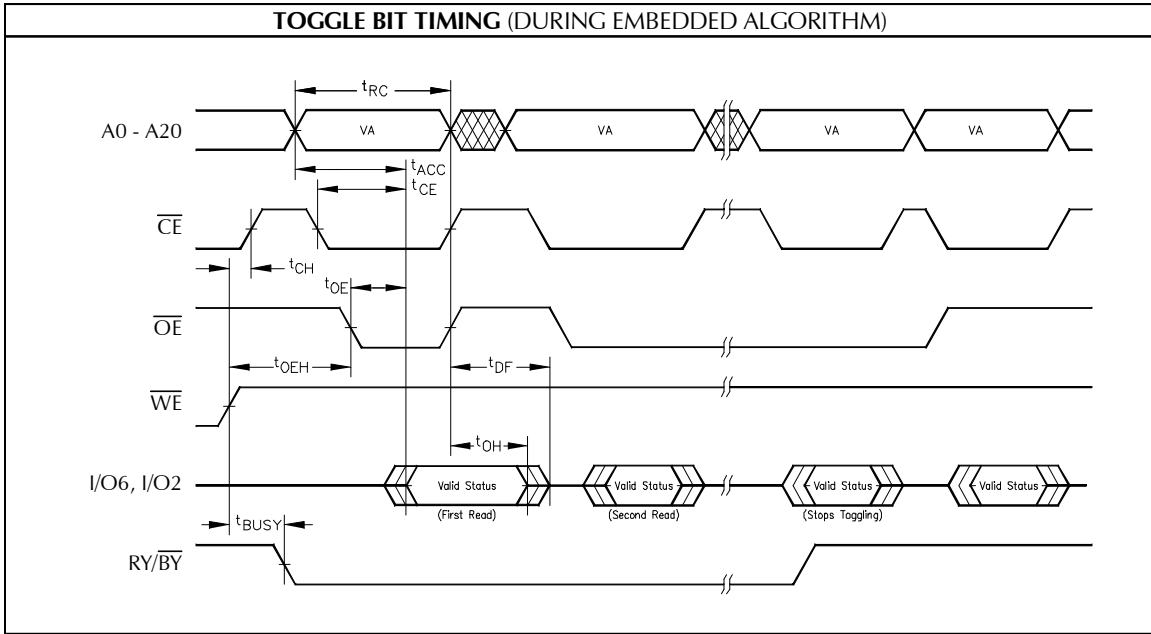


NOTE: When different from Sector Erase, Chip Erase listed in parentheses. SA = Sector Address. VA = Valid Address for reading status data.

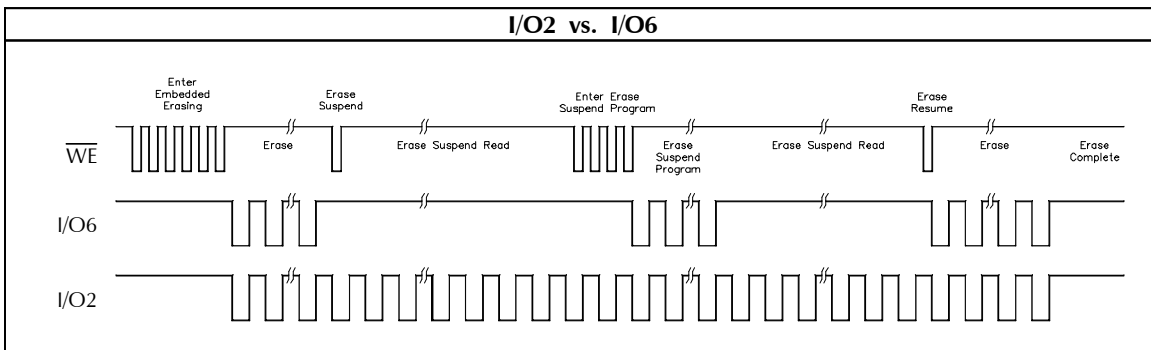


NOTE: VA = Valid Address. Illustration shows first two status cycle after command sequence, last status read cycle, and array data read cycle.

PRELIMINARY

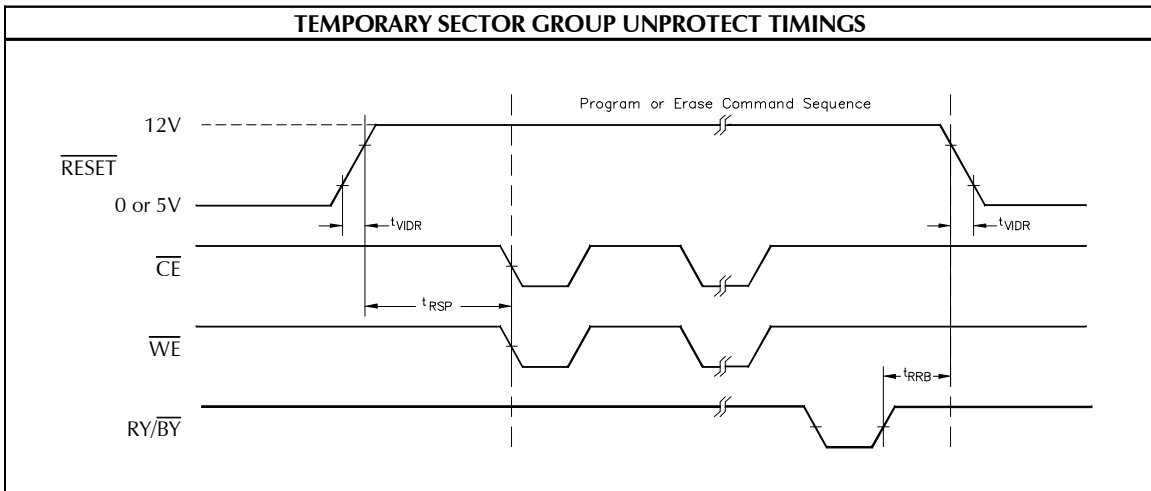


NOTE: VA = Valid Address; not required for I/O6¹. Illustration shows first two status cycle after command sequence, last status read cycle, and array data read cycle.



AC OPERATING CONDITIONS AND CHARACTERISTICS - TEMPORARY SECTOR UNPROTECT											
No.	Symbol	Parameter	70ns		90ns		12ns		150ns		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
30	t_{VIDR}	V_{ID} Rise and Fall Time ⁶	500		500		500		500		ns
31	t_{RSP}	RESET Setup Time for Temporary Sector Unprotect	4		4		4		4		μ s

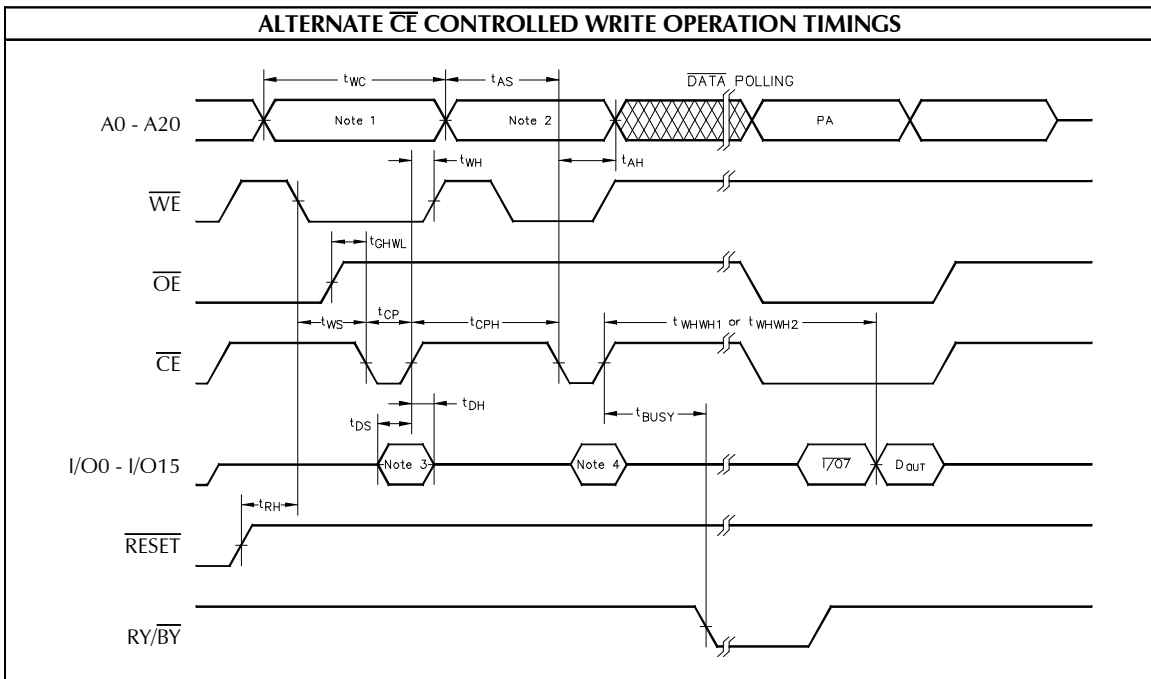
* $V_{DD} = 5.0V \pm 5\%$.



PRELIMINARY

AC OPERATING CONDITIONS AND CHARACTERISTICS - ERASE/PROGRAM OPERATION															
No.	Symbol	Parameter	70ns*			90ns			120ns			150ns			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
32	t _{WC}	Write Cycle Time ⁶	70			90			120			150			ns
33	t _{AS}	Address Set-up Time	0			0			0			0			ns
34	t _{AH}	Address Hold Time	40			45			50			50			ns
35	t _{DS}	Data Setup Time	40			45			50			50			ns
36	t _{DH}	Data Hold Time	0			0			0			0			ns
37	t _{GHEL}	Read Recover Time before Write	0			0			0			0			ns
38	t _{WS}	Chip Enable Setup Time	0			0			0			0			ns
39	t _{WH}	Chip Enable Hold Time	0			0			0			0			ns
40	t _{CP}	Write Pulse Width	40			45			50			50			ns
41	t _{CPH}	Write Pulse Width High	20			20			20			20			ns
42	t _{WHWH1}	Byte Programming Operation		7			7			7			7		μs
43	t _{WHWH2}	Sector Erase Operation		1	8			1	8				1	8	sec

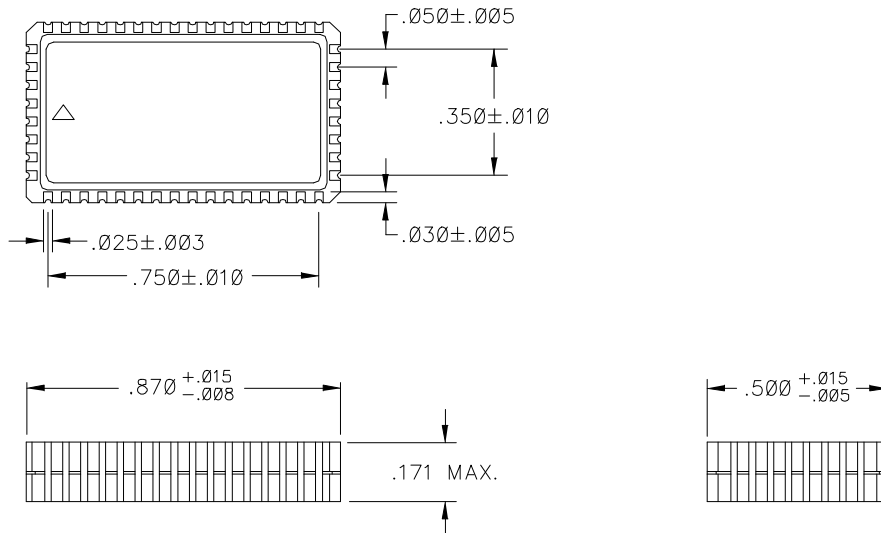
* V_{DD} = 5.0V ± 5%.
See the Erase and Programming Performance Section for more information.



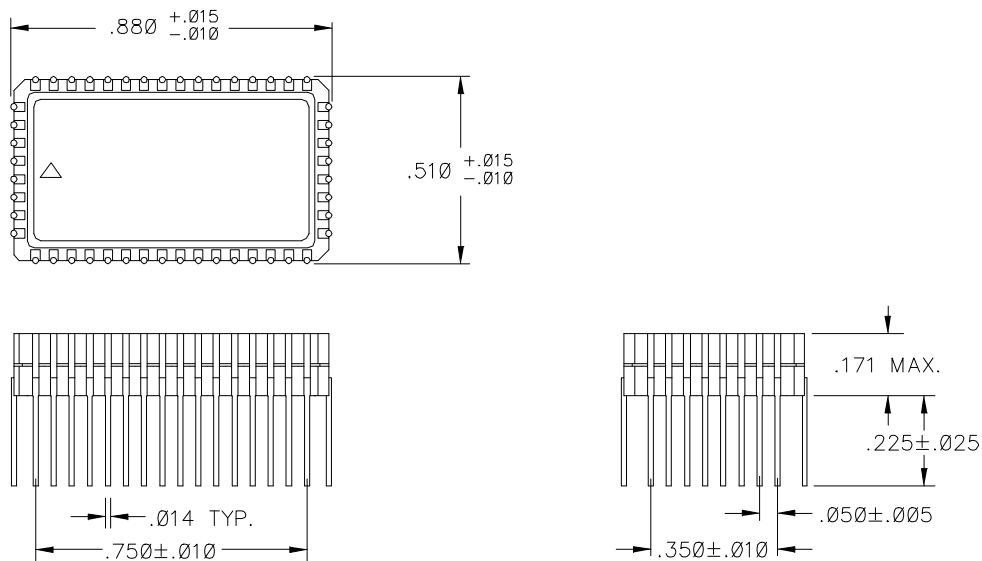
- Notes:**
1. 555 for Program, 2AA for Erase.
 2. Program Address for Program, Sector Address for Sector Erase, 555 for Chip Erase.
 3. A0 for Program, 55 for Erase.
 4. Program Data for Program, 30 for Sector Erase, 10 for Chip Erase.
 5. PA = Program Address, I/O7 = Complement of Data Input, D_{OUT} = Array Data.

PRELIMINARY

(48 - Pin Leadless SLCC) MECHANICAL DIAGRAM

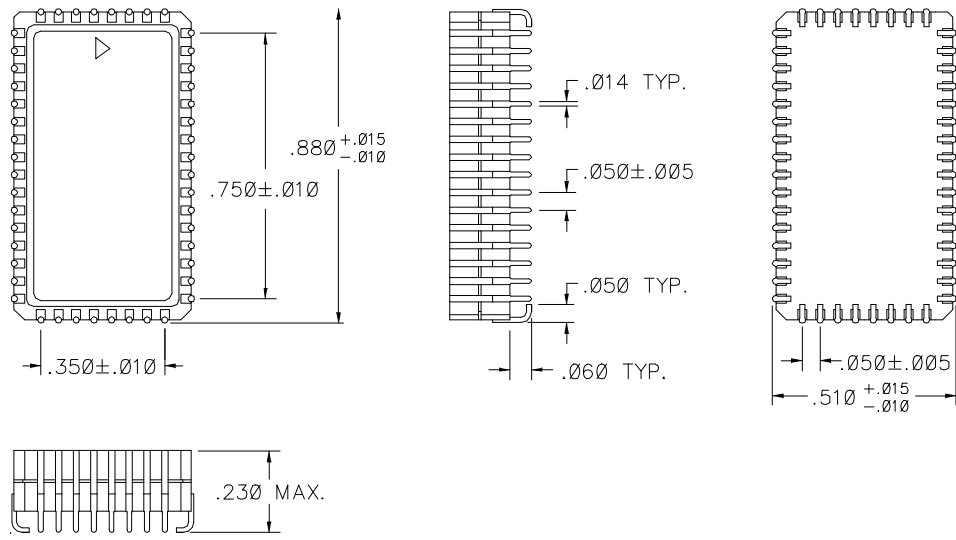


(48 - Pin Straight Leaded SLCC) MECHANICAL DIAGRAM

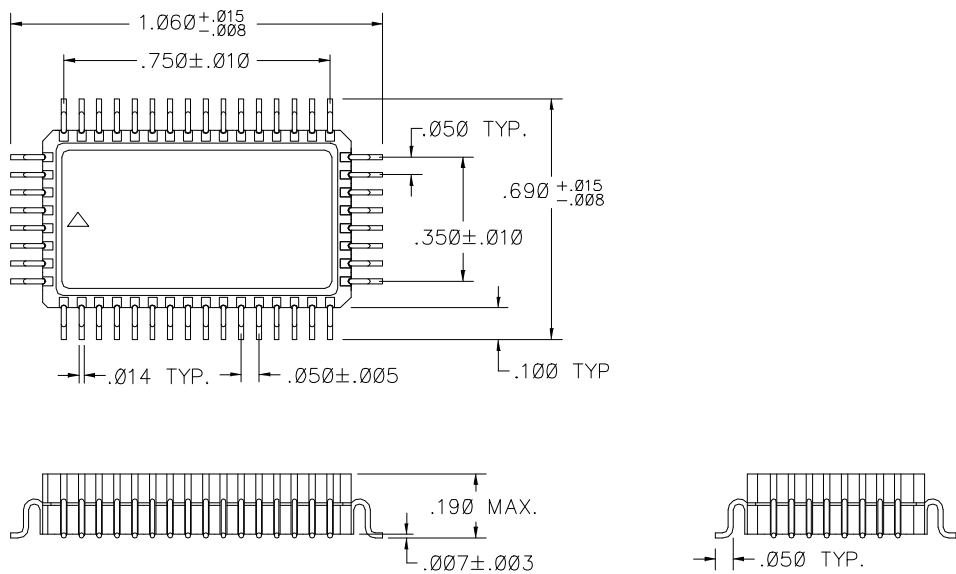


PRELIMINARY

(48 - Pin J Leaded SLCC) MECHANICAL DIAGRAM

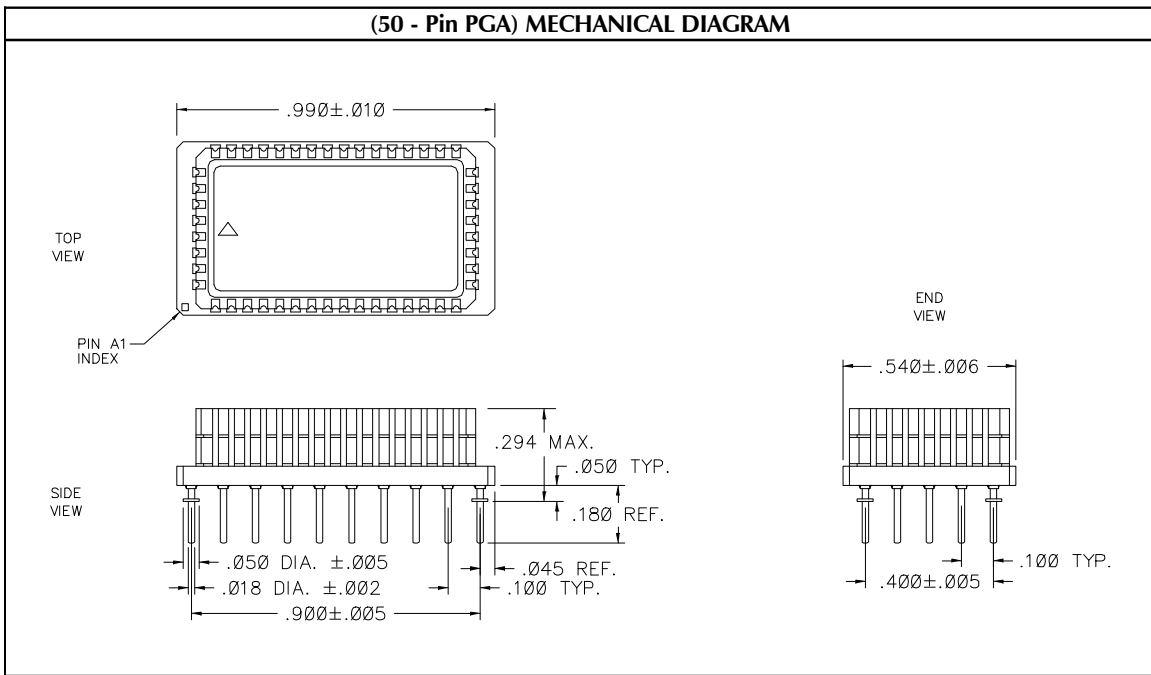


(48 - Pin Gullwing Leaded SLCC) MECHANICAL DIAGRAM

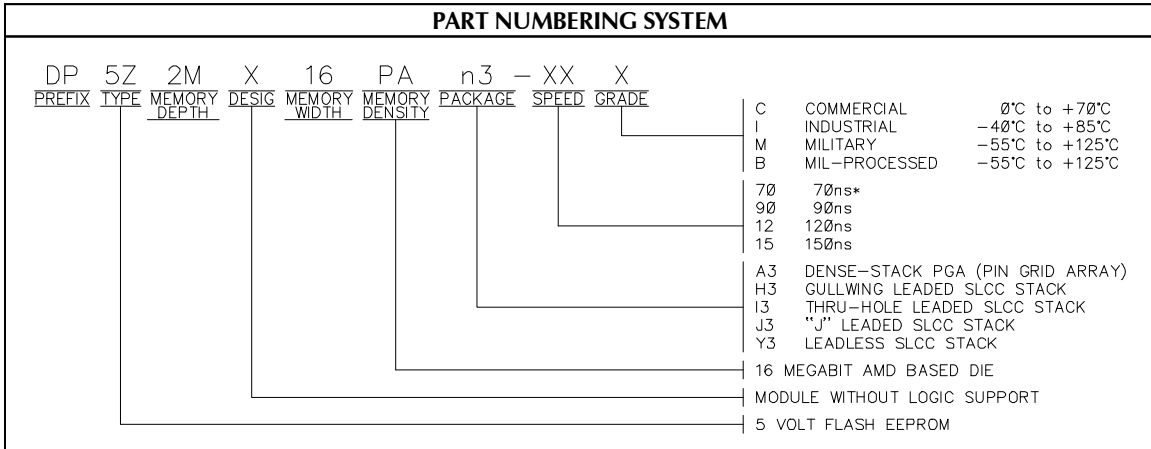


PRELIMINARY

(50 - Pin PGA) MECHANICAL DIAGRAM



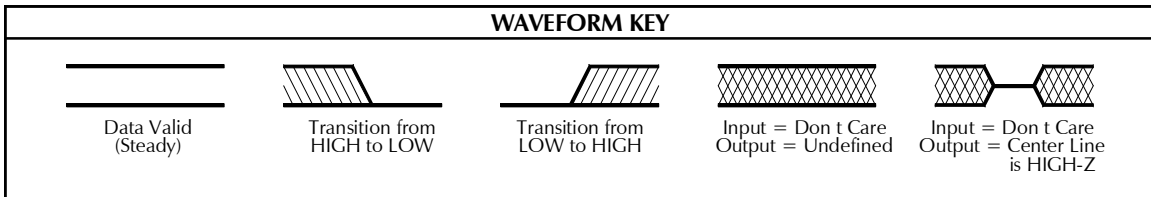
PRELIMINARY



* V_{DD} = 5.0V ± 5%.

Notes:

- All voltages are with respect to V_{SS}.
- Minimum DC voltage on input or I/O pins is -0.5 V. During voltage transitions, inputs may overshoot V_{SS} to -2.0V for periods of up to 20ns. Maximum DC voltage on output and I/O pins is V_{DD}+0.5V. During voltage transitions, outputs may overshoot to V_{DD}+2.0V for periods up to 20ns.
- Minimum DC input voltage on A9, OE, RESET pins is -0.5V. During voltage transitions, A9, OE, RESET pins may overshoot V_{SS} to -2.0V for periods of up to 20ns. See Maximum DC Input Voltage on A9, OE, and RESET is 12.5V which may overshoot to 13.5V for periods up to 20ns.
- No more than one output shorted at a time. Duration of the short circuit should not be greater than one second.
- Stresses greater than those under **ABSOLUTE MAXIMUM RATINGS** may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- This parameter is guaranteed and not 100% tested.
- The I_{CC} current listed includes both the DC Operating Current and the frequency dependent component (at 6MHz). The frequency component typically is less than 1mA/MHz, with OE at V_{IH}.
- I_{CC} active while Embedded Program or Embedded Erase algorithm is in progress.
- This module is comprised of multiple 2Meg X 8 FLASH memory devices. The functional descriptions contained in this document are for a single FLASH memory device. When using this module, each device must be managed separately. If a function is to be performed in 16-bit mode, all commands must be written to each memory device. Example: When programming the module, the program command A0H should be written to the module as A0A0H followed by the 16-bit program. A single device can be programmed or erased by writing the appropriate 8-bit command to that device. After a program or erase operation has begun, the status bits for each device that is being programmed or erased must be monitored individually (See Table 5, Write Operation Status).



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